

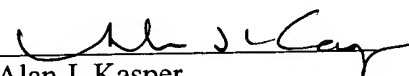
PRELIMINARY AMENDMENT
Attorney Docket No.: Q68148

REMARKS

Accordingly, early and favorable consideration of the presently pending claims is respectfully requested.

Respectfully submitted,

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APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

6. A single crystal SiC, wherein:
the single crystal SiC is obtained by a method claimed in ~~any one of~~ claims 1 ~~through~~ 5,
and
the planar defect density of a topmost surface falls within a range not higher than $10^3/\text{cm}^2$.
7. A single crystal SiC, comprising:
single crystal SiC obtained by a method claimed in ~~any one of~~ claims 1 ~~through~~ 5, and
another SiC deposited on the single crystal SiC by the vapor phase growth method or the
liquid phase growth method.
10. A SiC composite material, comprising:
single crystal SiC produced by a method claimed in ~~any one of~~ claims 1 ~~through~~ 5, and
diamond or GaN formed on the single crystal SiC.

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